

N- and P-Channel 60-V (D-S) MOSFET

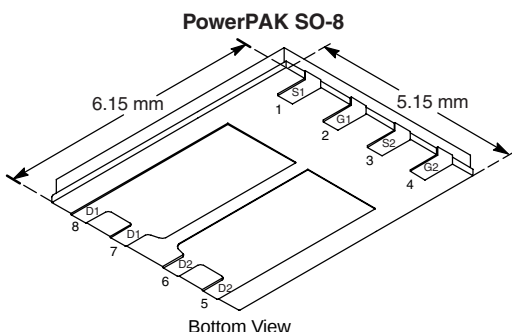
PRODUCT SUMMARY				
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)
N-Ch	60	0.075 at V _{GS} = 10 V	4.6	12 nC
		0.100 at V _{GS} = 4.5 V	4.0	
P-Ch	- 60	0.064 at V _{GS} = - 10 V	- 5.0	47
		0.080 at V _{GS} = - 4.5 V	- 4.5	

FEATURES

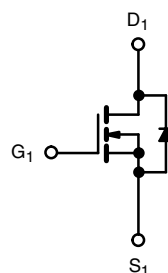
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET
- New Low Thermal Resistance PowerPAK® Package with Low 1.07 mm Profile
- 100 % R_g Tested



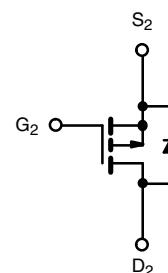
RoHS
COMPLIANT
HALOGEN
FREE
Available



Ordering Information: Si7530DP-T1-E3 (Lead (Pb)-free)
Si7530DP-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted							
Parameter		Symbol	N-Channel		P-Channel		Unit
			10 s	Steady	10 s	Steady	
Drain-Source Voltage		V _{DS}	60		- 60		V
Gate-Source Voltage		V _{GS}	± 20				
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25°C	I _D	4.6	3.0	- 5.0	- 3.2	A
	T _A = 70°C		3.6	2.4	- 4.0	- 2.6	
Pulsed Drain Current		I _{DM}	15		- 25		
Continuous Source Current (Diode Conduction) ^a		I _S	2.7	1.2	- 2.9	- 1.2	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	15		- 22		mJ
Single Pulse Repetitive Avalanche Energy ^b		E _{AS}	11		24.2		
Maximum Power Dissipation ^a	T _A = 25°C	P _D	3.3	1.4	3.5	1.5	W
	T _A = 70°C		2.1	0.9	2.2	0.94	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150				°C
Soldering Recommendations (Peak Temperature) ^{c, d}			260				

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	N-Channel		P-Channel		Unit
			Typical	Maximum	Typical	Maximum	
Maximum Junction-to-Ambient ^a	t ≤ 10 s	R _{thJA}	29	38	27	36	°C/W
	Steady State		60	85	60	85	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	4.0	5.2	3.3	4.3	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. Duty Cycle ≤ 1 %.

c. See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

d. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions		Min.	Typ.	Max.	Unit	
Static								
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	N-Ch	1		3	V	
		V _{DS} = V _{GS} , I _D = - 250 μA	P-Ch	- 1		- 3		
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	N-Ch P-Ch			± 100 ± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V	N-Ch			1	μA	
		V _{DS} = - 60 V, V _{GS} = 0 V	P-Ch			- 1		
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 55°C	N-Ch			5		
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 55°C	P-Ch			- 5		
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	N-Ch	15			A	
		V _{DS} ≤ - 5 V, V _{GS} = - 10 V	P-Ch	- 25				
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 4.6 A	N-Ch		0.060	0.075	Ω	
		V _{GS} = - 10 V, I _D = - 5.0 A	P-Ch		0.051	0.064		
		V _{GS} = 4.5 V, I _D = 4.0 A	N-Ch		0.080	0.100		
		V _{GS} = - 4.5 V, I _D = - 4.5 A	P-Ch		0.064	0.080		
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 4.6 A	N-Ch		6		S	
		V _{DS} = - 15 V, I _D = - 5.0 A	P-Ch		16			
Diode Forward Voltage ^a	V _{SD}	I _S = 2.7 A, V _{GS} = 0 V	N-Ch		0.85	1.2	V	
		I _S = - 2.9 A, V _{GS} = 0 V	P-Ch		- 0.85	- 1.2		
Dynamic ^b								
Total Gate Charge	Q _g	N-Channel V _{DS} = 30 V, V _{GS} = 10 V, I _D = 15 A	N-Ch P-Ch		12 26	20 40	nC	
Gate-Source Charge	Q _{gs}		N-Ch P-Ch		2 4.5			
Gate-Drain Charge	Q _{gd}	P-Channel V _{DS} = - 30 V, V _{GS} = - 10 V, I _D = - 5.0 A	N-Ch P-Ch		3.5 7			
Gate Resistance	R _g	f = 1.0 MHz	N-Ch P-Ch	0.6 3.5	1.5 7	2.5 11	Ω	
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 30 V, R _L = 30 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 6 Ω	N-Ch P-Ch		7 8	15 15	ns	
Rise Time	t _r		N-Ch P-Ch		8 9	15 15		
Turn-Off Delay Time	t _{d(off)}	P-Channel V _{DD} = - 30 V, R _L = 30 Ω I _D ≅ - 1 A, V _{GEN} = - 10 V, R _g = 6 Ω	N-Ch P-Ch		15 65	25 100		
Fall Time	t _f		N-Ch P-Ch		7 30	20 45		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.7 A, dI/dt = 100 A/μs	N-Ch		30	60		
		I _F = - 5 A, dI/dt = 100 A/μs	P-Ch		40	80		
Reverse Recovery Energy	Q _{rr}	I _F = 2.7 A, dI/dt = 100 A/μs	N-Ch		33	66	pC	
		I _F = - 5 A, dI/dt = 100 A/μs	P-Ch		57	115		

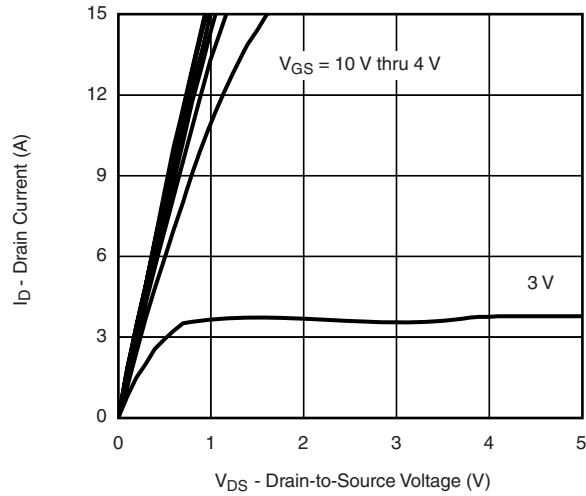
Notes:

a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

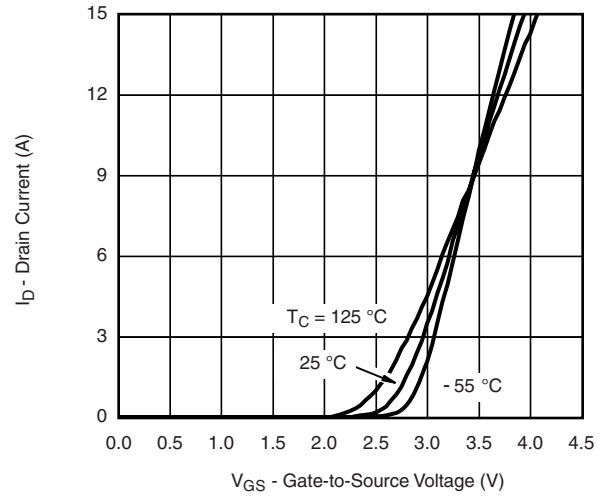
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

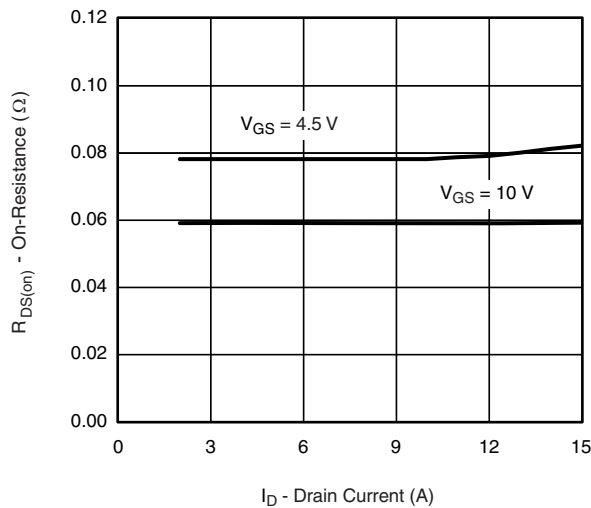
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



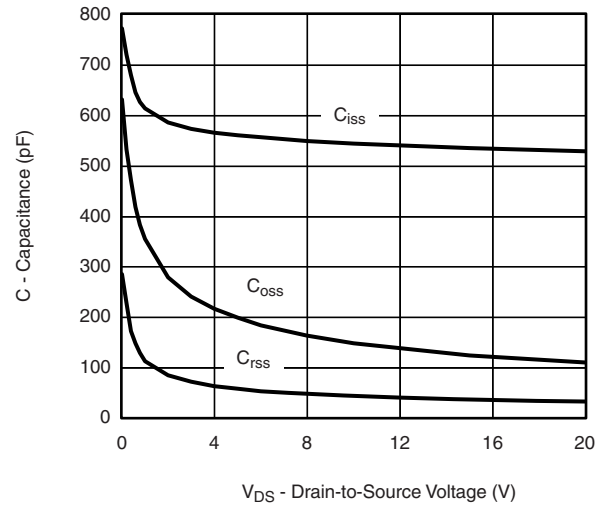
Output Characteristics



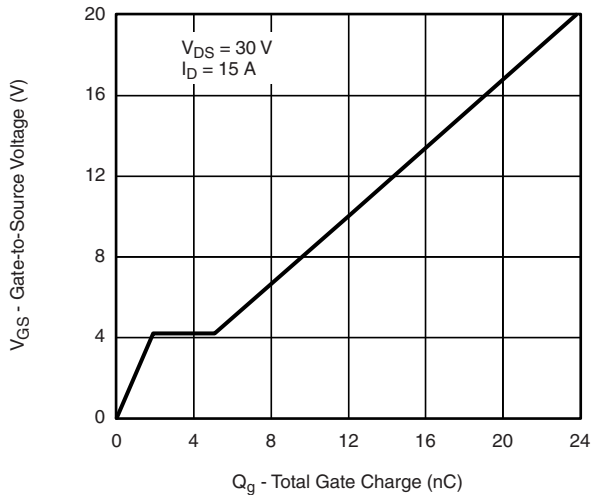
Transfer Characteristics



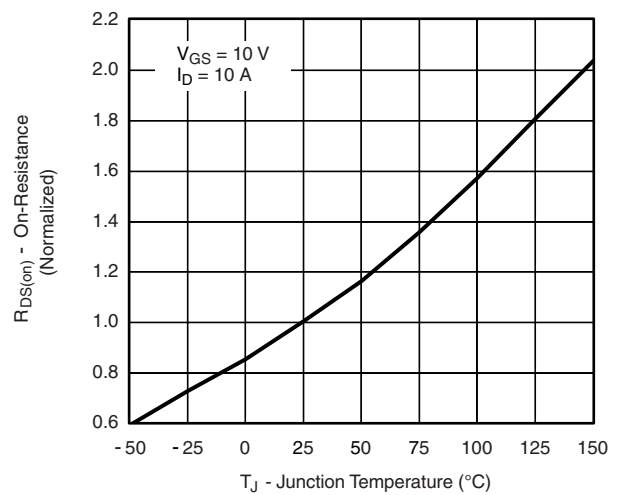
On-Resistance vs. Drain Current



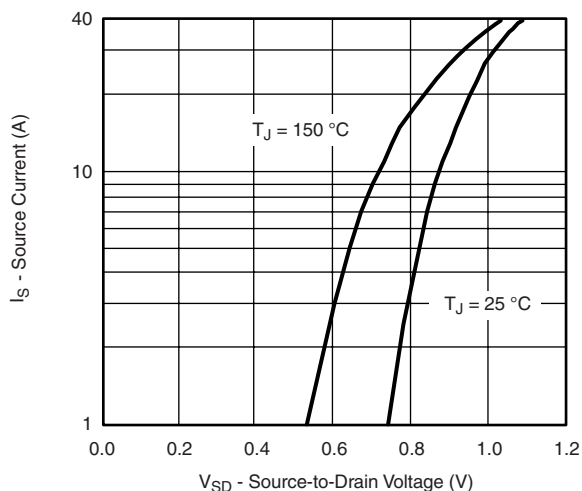
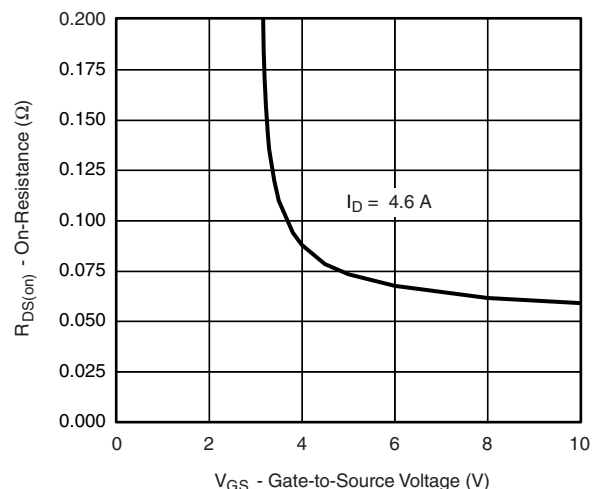
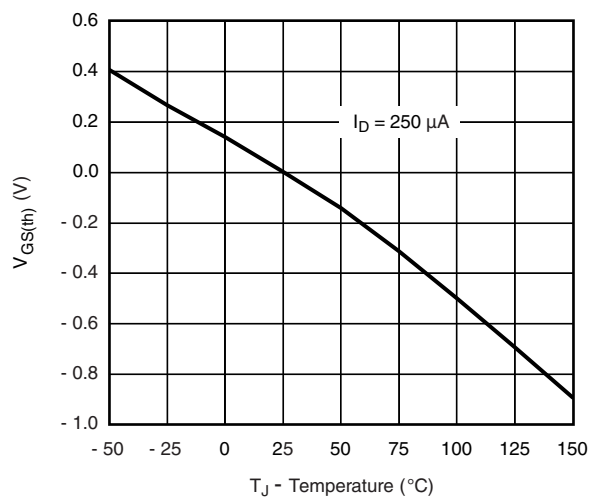
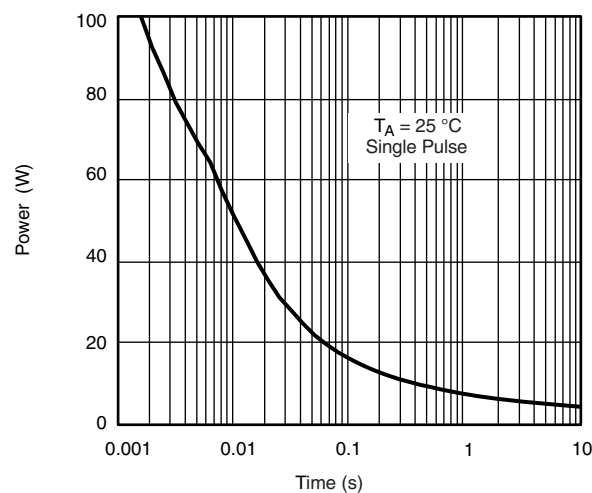
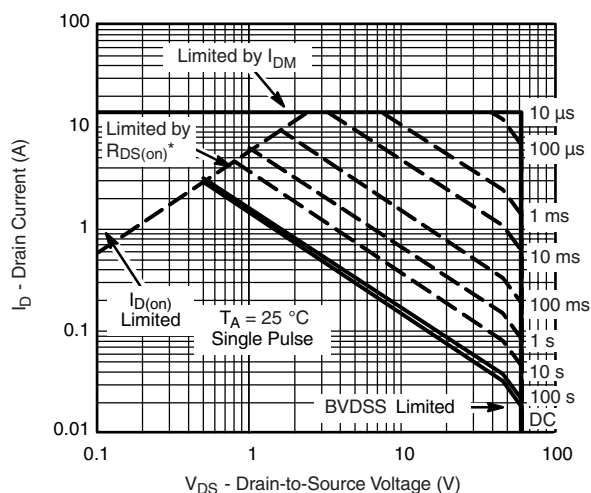
Capacitance



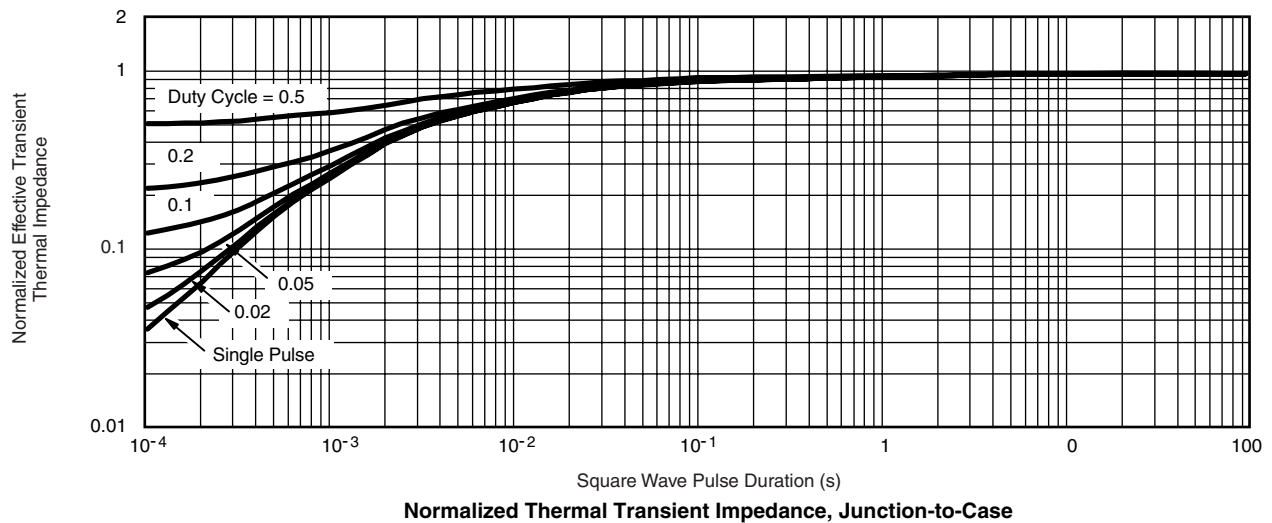
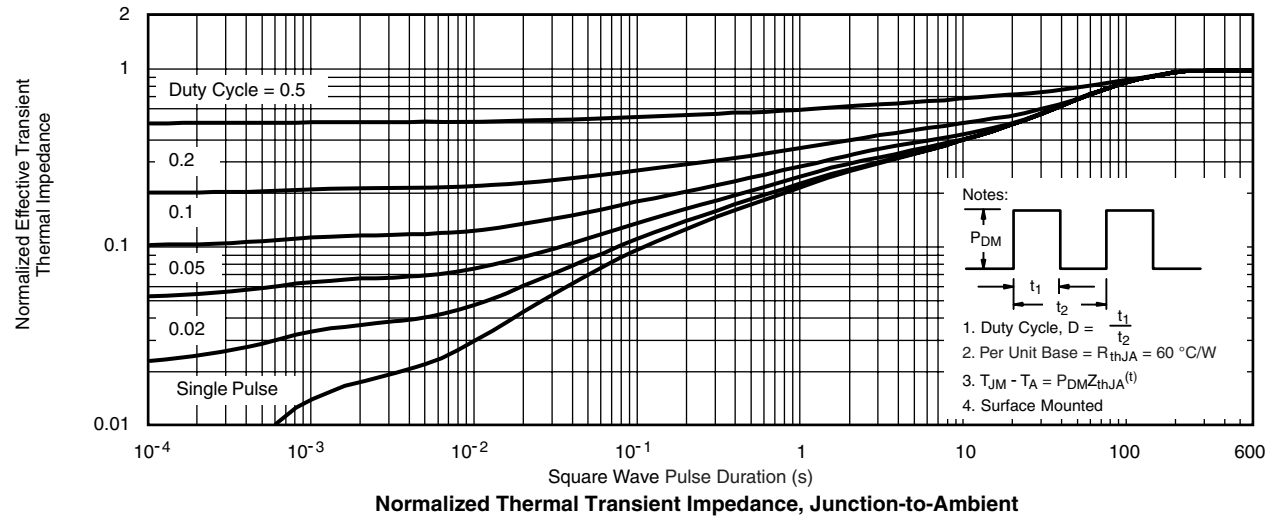
Gate Charge

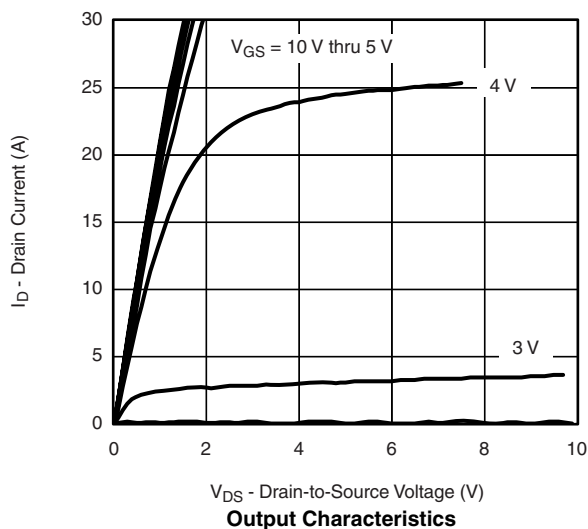
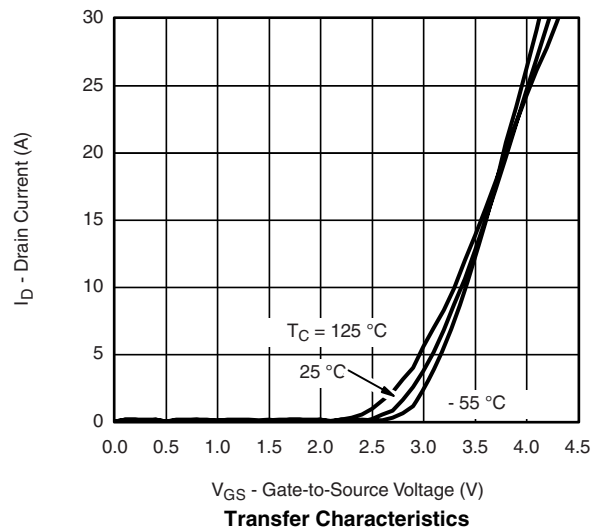
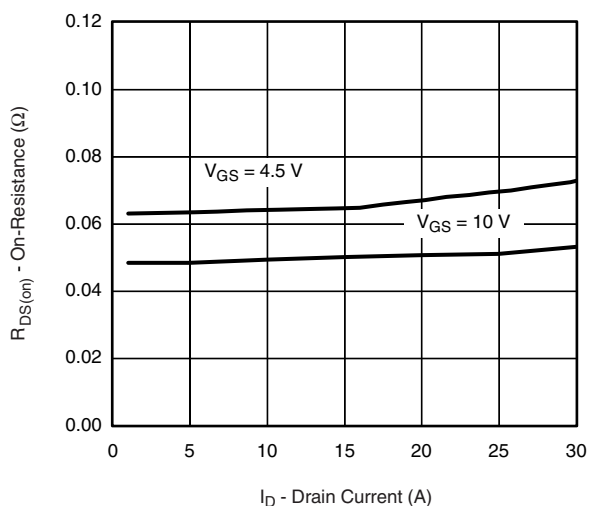
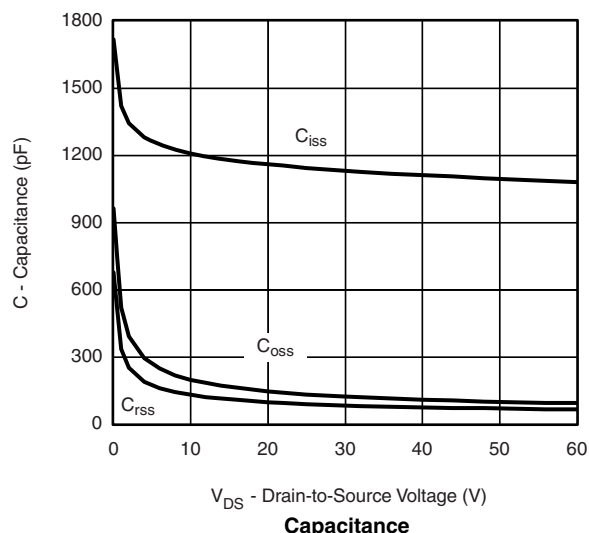
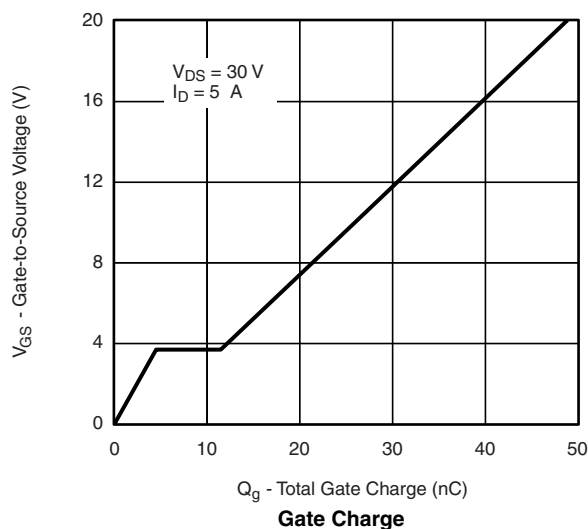
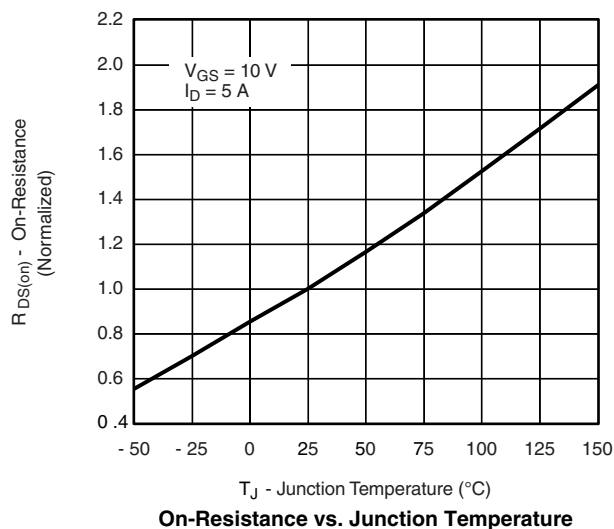


On-Resistance vs. Junction Temperature

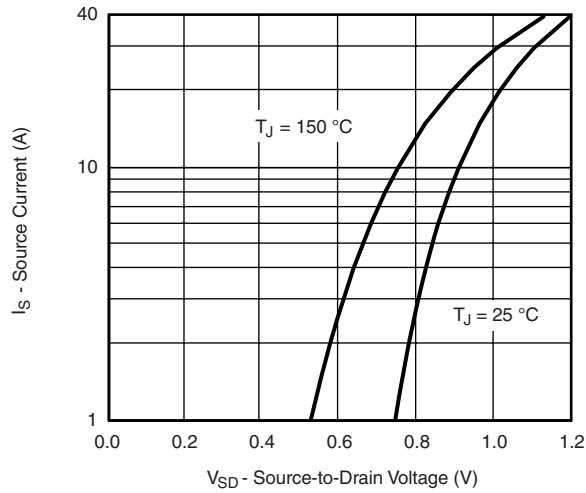
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power*** $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified**Safe Operating Area, Junction-to-Case**

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

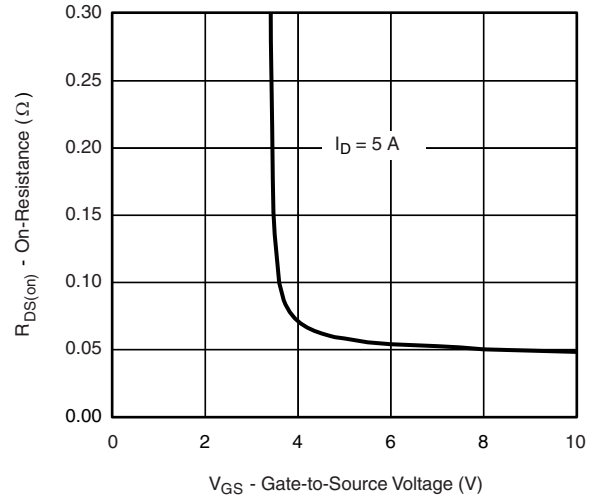


P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**

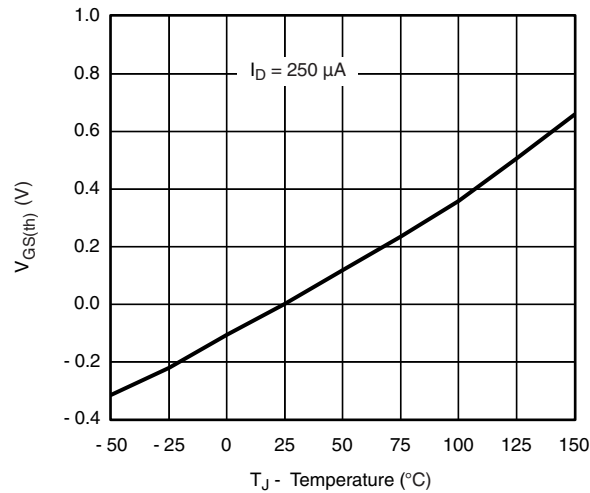
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



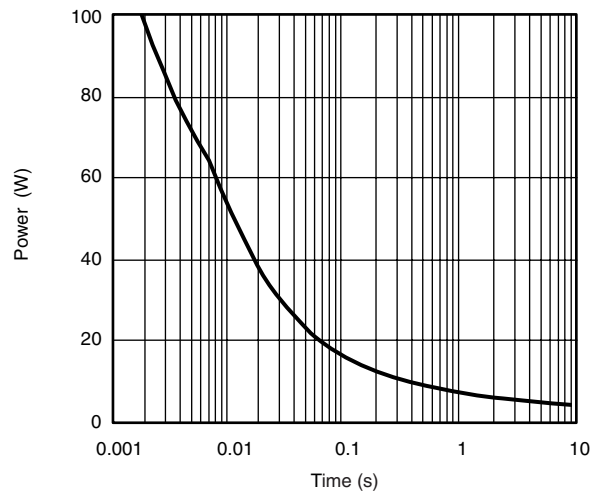
Source-Drain Diode Forward Voltage



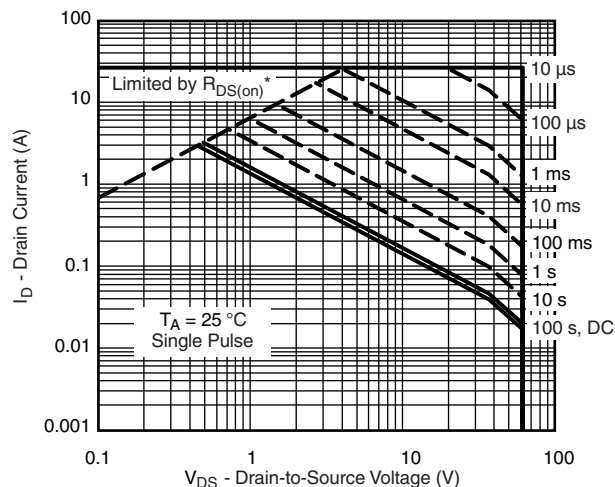
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

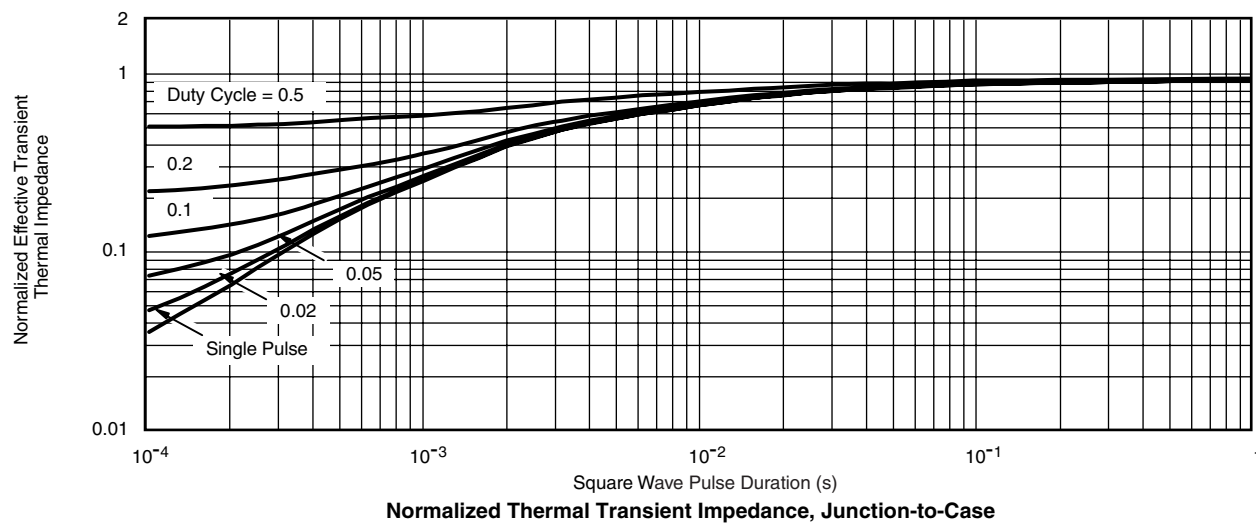
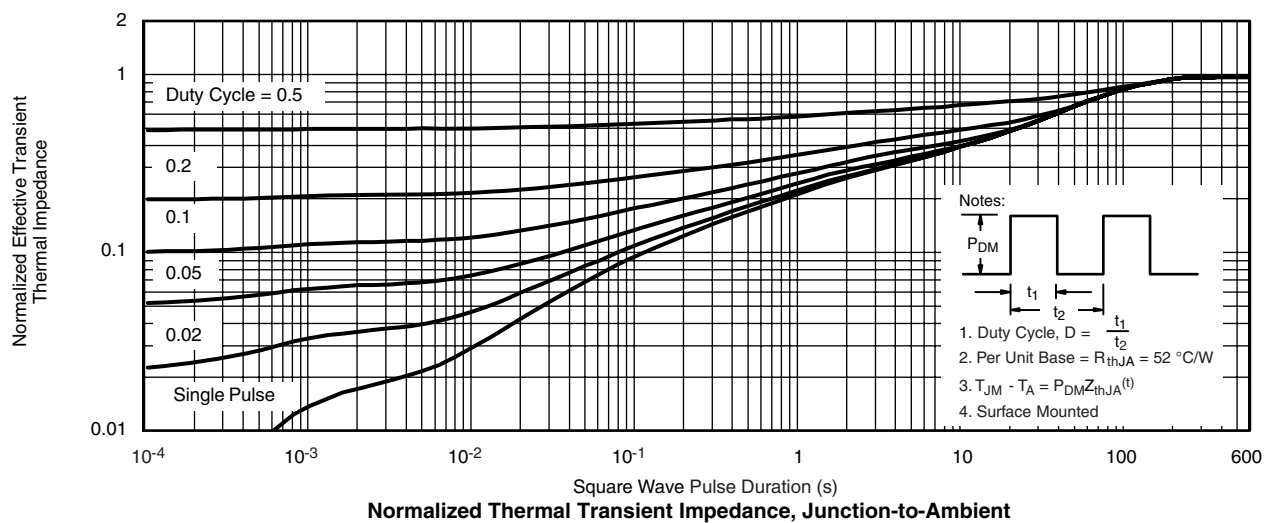


Single Pulse Power, Junction-to-Ambient



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?73249.



Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.